

Pimpri Chinchwad Education Trust's

PIMPRI CHINCHWAD COLLEGE OF ENGINEERING

SECTOR NO. 26, PRADHIKARAN, NIGDI, PUNE 411044

An Autonomous Institute Approved by AICTE and Affiliated to SPPU, Pune

**DEPARTMENT OF ELECTRONICS AND TELECOMMUNICATION
ENGINEERING**



Curriculum Structure and Syllabus Honors

in

**Semiconductor Technology
(Regulations 2023)**



**Effective from Academic Year 2025-26
(Updated with minor Changes)**

Institute Vision

To be one of the top 100 Engineering Institutes of India in coming five years by offering exemplarily Ethical, Sustainable and Value Added Quality Education through a matching ecosystem for building successful careers.

Institute Mission

1. Serving the needs of the society at large through establishment of a state-of-art Engineering Institute.
2. Imparting right Attitude, Skills, Knowledge for self-sustenance through Quality Education.
3. Creating globally competent and Sensible engineers, researchers and entrepreneurs with an ability to think and act independently in demanding situations.

EOMS Policy

“We at PCCOE are committed to offer exemplarily Ethical, Sustainable and Value Added Quality Education to satisfy the applicable requirements, needs and expectations of the Students and Stakeholders.


We shall strive for technical development of students by creating globally competent and sensible engineers, researchers and entrepreneurs through Quality Education.

We are committed for Institute’s social responsibilities and managing Intellectual property.

We shall achieve this by establishing and strengthening state-of-the-art Engineering Institute through continual improvement in effective implementation of Educational Organizations Management Systems (EOMS).”


Course Approval Summary

Board of Studies - Department of E&TC Engineering

Sr. No.	Name of the Course	Course Code	Page number	Signature and stamp of BoS chairman
1	Digital Integrated Circuits	BET25HN11/ BET25HN11	7	 Chairman BoS, Electronics & Telecommunication Engineering PCET's, Pimpri Chinchwad College of Engineering Sector No. 26, Pradhikaran, Nigdi, Pune-44
2	Digital Integrated Circuits Lab	BET25HN12/ BET25HN12	9	
3	Analog Circuits and Advance MOS Devices	BET26HN11/ BET26HN11	11	
4	Analog Circuits and Advance MOS Devices Lab	BET26HN12/ BET26HN12	13	
5	VLSI Physical Design and fabrication techniques	BET27HN11/ BET28HN12	15	
6	Seminar	BET27HN12/ BET28HN13	17	
7	Project	BET28HN11/ BET27HN13	18	

Approved by Academic Council:

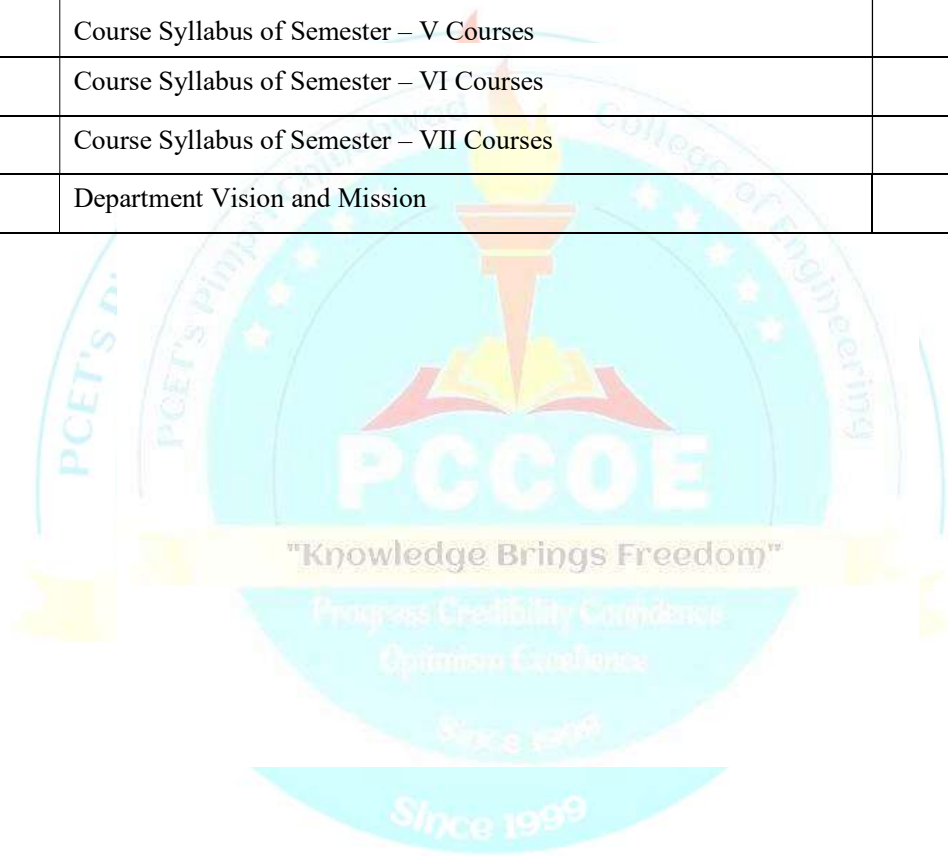
"Knowledge Brings Freedom"


Chairman
Academic Council
 PCET's, Pimpri Chinchwad College of Engineering
 Sector No. 26, Pradhikaran, Nigdi, Pune-44

Chairman, Academic Council
 Pimpri Chinchwad College of Engineering, Pune

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Preface

With rapid evolution in technologies and an increasing demand for latest innovation in products and services, the semiconductor manufacturing industry is expected to rise. From smart phones to cars, manufacturers and the semiconductor industry are ramping up to meet the world's seemingly insatiable demand for chips. Semiconductor chips have become essential to everyday lives and that dependence is predicted to grow to cater industry demands. Emerging markets and technologies such as AI, robotic process automation and 5G connectivity are also fueling the growth of the semiconductor industry. From a recruitment perspective, several new jobs are being created across sectors and across specializations.

For Honors degree program, student has to earn additional 20 credits in emerging area of one's own domain.

Objectives of Honors Degree

1. To enable students to pursue allied academic interest in contemporary areas.
2. To provide effective yet flexible options for students to achieve basic to intermediate level competence in the contemporary area.
3. To enhance the employability skills with different combinations of competencies and flavors.
4. To provide an academic mechanism for fulfilling demand of specialized areas from industries for higher order skill jobs.
5. To provide a strong foundation to students aiming to pursue research/ higher studies in the contemporary field of study.

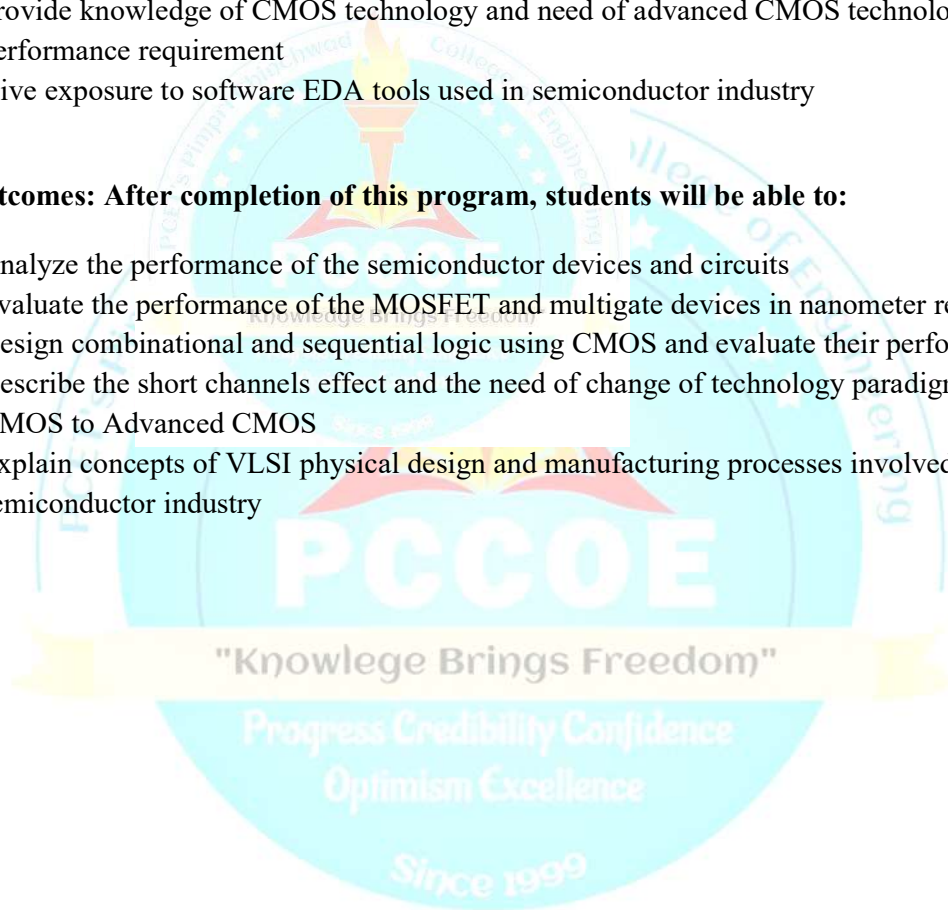
Semiconductor Technology

Objectives:

1. Introduce students to manufacturing processes involved in semiconductor industry
2. Explain semiconductor devices with its practical applications
3. Provide knowledge of CMOS technology and need of advanced CMOS technology to cater performance requirement
4. Give exposure to software EDA tools used in semiconductor industry

Outcomes: After completion of this program, students will be able to:

1. Analyze the performance of the semiconductor devices and circuits
2. Evaluate the performance of the MOSFET and multigate devices in nanometer region
3. Design combinational and sequential logic using CMOS and evaluate their performance.
4. Describe the short channels effect and the need of change of technology paradigm from CMOS to Advanced CMOS
5. Explain concepts of VLSI physical design and manufacturing processes involved in semiconductor industry





Curriculum Structure

Curriculum structure- Scheme-A

Sem-ester	Course Code	Course Name	Teaching Scheme					Evaluation Scheme						
			L	P	T	Hrs	CR	FA1	FA2	SA	TW	PR	OR	Total
V	BET25HN11	Digital Integrated Circuits	4	-	-	4	4	20	20	60	-	-	-	100
	BET25HN12	Digital Integrated Circuits Lab	-	2	-	2	1	-	-	-	25	-	25	50
VI	BET26HN11	Analog Circuits and Advance MOS Devices	4	-	-	4	4	20	20	60	-	-	-	100
	BET26HN12	Analog Circuits and Advance MOS Devices Lab	-	2	-	2	1	-	-	-	25	-	25	50
VII	BET27HN11	VLSI Physical Design and fabrication techniques	4	-	-	4	4	20	20	60	-	-	-	100
	BET27HN12	Seminar	-	4	-	4	2	-	-	-	-	-	50	50
VIII	BET28HN11	Project	-	8	-	8	4	-	-	-	100	-	50	150
Total			12	16		28	20	-	-	-	-	-	-	600

Abbreviations:

1 Lecture hour = 1 Credit 2 Lab Hours = 1 Credit 1 Tutorial Hour = 1 Credit
 Abbreviations are: L-Lecture, P-Practical, T-Tutorial, H- Hours, FA-Formative Assessment, SA-Summative assessment TW –Term work, OR – Oral, CR- Credits

Curriculum structure- Scheme-B

Sem-ester	Course Code	Course Name	Teaching Scheme					Evaluation Scheme						
			L	P	T	Hrs	CR	FA1	FA2	SA	TW	PR	OR	Total
V	BET25HN11	Digital Integrated Circuits	4	-	-	4	4	20	20	60	-	-	-	100
	BET25HN12	Digital Integrated Circuits Lab	-	2	-	2	1	-	-	-	25	-	25	50
VI	BET26HN11	Analog Circuits and Advance MOS Devices	4	-	-	4	4	20	20	60	-	-	-	100
	BET26HN12	Analog Circuits and Advance MOS Devices Lab	-	2	-	2	1	-	-	-	25	-	25	50
VII	BET27HN13	Project	-	8	-	8	4	-	-	-	100	-	50	150
VIII	BET28HN12	VLSI Physical Design and fabrication techniques	4	-	-	4	4	20	20	60	-	-	-	100
	BET28HN13	Seminar	-	4	-	4	2	-	-	-	-	-	50	50
Total			12	16		28	20	-	-	-	-	-	-	600

PCGOE
"Knowledge Brings Freedom"

Progress Credibility Confidence
Optimism Excellence

Since 1999



Course Syllabus

Semester - V

"Knowledge Brings Freedom"

Progress Credibility Confidence

Optimism Excellence

Since 1974

Program:	B. Tech. (E&TC-Honors)			Semester:	V		
Course:	Digital Integrated Circuits			Code:	BET25HN11		
Teaching Scheme (Hrs./Week)				Evaluation Scheme and Marks			
Credit	Lecture	Practical	Practical	FA		SA	Total
				FA1	FA2		
4	4	-	-	20	20	60	100
Prior Knowledge of: Basics of semiconductor Physics, Digital Electronics is essential.							
Course Objectives: <ol style="list-style-type: none"> To emphasize on fundamental principles of MOSFET To understand short channel effects in MOSFET in nanometer region To focus on the design combinational and sequential logic gates using CMOS and its related timing issues 							
Course Outcomes: After the completion of the course, the students will be able to: <ol style="list-style-type: none"> Describe Working principle of MOSFET Device Explain short channel effects in MOSFET in nanometer regime Analyze CMOS inverter performance with respect to technology scaling in nanometer region Design combinational and sequential logic gates using CMOS Describe timing issues and clock distribution techniques in digital circuits Design Arithmetic building blocks 							
Detailed Syllabus:							
Unit	Description						Durat ion
1.	MOSFET Device: MOSFET Structure and Operation, MOSFET: I-V Characteristics MOS transistor under static condition, Dynamic behavior, MOS structure capacitances, Actual MOS transistor-some secondary effects, SPICE models.						11
2.	MOSFET in nanometer: Scaling and its impact, Short channel effects, Drain induced barrier lowering, sub-threshold leakage, punch through effect, hot carrier effect						9
3.	Circuit Perspective: CMOS Inverter, Performance of CMOS Inverter, Power, Energy, Energy-Delay, Technology Scaling and its Impact on the Inverter Metrics						11
4.	DESIGNING COMBINATIONAL & SEQUENTIAL LOGIC GATES In CMOS: Static CMOS Design, Dynamic CMOS Design, Power Consumption in CMOS Gates, Static Latches and Registers, Dynamic Latches and Registers						9
5.	TIMING ISSUES IN DIGITAL CIRCUITS: Introduction, Synchronous Timing basics, Clock Skew and Jitter, Clock distribution techniques, Clock Generation and Synchronization.						11
6.	Designing Arithmetic building blocks: Adder, Multiplier, Shifter, Power and Speed tradeoff in datapath structure						9
	Total						60

Text Books:

1. Jan M Rabaey, Digital Integrated Circuits, 2nd Edition, Pearson Education, 2003.
2. Sung-Mo Kang, CMOS Digital Integrated Circuits, 3rd Edition, McGraw-Hill, 2003.

Reference Books:

1. Neil H.E.Weste and Kamran Eshraghian, Principles of CMOS VLSI Design, A System Perspective, Pearson Education, India.
4. Ken Martin, Digital Integrated Circuits, Oxford Press.
2. CMOS Circuit Design, Layout and simulation: J. Baker, D.E. Boyce., IEEE press.
3. Semiconductor physics and Devices, Donald Neamen, McGraw-Hill, 3rd edition.



Department of E&TC Engineering

Program:	B. Tech. (E&TC-Honors)			Semester:	VI		
Course:	Digital Integrated Circuits Lab			Code:	BET25HN12		
	Teaching Scheme (Hrs./Week)			Evaluation Scheme and Marks			
Credit	Lecture	Practical	Tutorial	TW	OR	PR	Total
01	--	02	-	25	25	--	50
Prior knowledge of: Analog circuits and semiconductor devices							
Objectives: To design and analyze performance of combinational and sequential CMOS circuits							
Outcomes: At the end of Laboratory work, the students will be able to: CO 1: Design CMOS Circuits such as inverter and analyze its characteristics CO 2: Design logic gates using different logic design styles to verify their performance CO 3: Design and Simulate Combinational circuits using EDA tool. CO4 : Design and Simulate sequential circuits using EDA tool							
Detailed Syllabus:							
Expt. No.	List of Experiments						
1	Design and Simulation of CMOS Inverter to study the transfer Characteristics by varying the design constraints using EDA Tools						
2	Design and Simulation of logic gates using various logic styles and compare its performance						
3	Develop HDL model, Simulate and Synthesize 32-bit Parallel adder using 8-bit adder module						
4	Design and Simulate 32-bit Shift register using 8-bit Shift register module						
Reference Books:							
<ol style="list-style-type: none"> 1. Samir Palnitkar, Verilog HDL, 2nd Edition, Pearson Education, 2003. 2. Douglas Perry, VHDL: Programming by Example, 2017 							



Course Syllabus

Semester - VI

Department of E&TC Engineering

Program:	B.Tech.(E&TC) - B. Tech. (E&TC-Honors)			Semester:	VI		
Course:	Analog Circuits and Advance MOS Devices			Code:	BET26HN11		
	Teaching Scheme (Hrs./Week)			Evaluation Scheme and Marks			
Credit	Lecture	Practical	Tutorial	FA		SA	Total
				FA1	FA2		
4	4	-	-	20	20	60	100
Prior Knowledge of: Basic knowledge of Analog Electronics and CMOS Devices.							
Course Objectives: To acquaint the students with basic CMOS analog building blocks and analog sub-system design. To make the students understand challenges with MOSFET in nanometer regime To interpret the performance parameters and challenges of multi-gate devices							
Course Outcomes: After the completion of the course, the students should be able to: CO1: Understand the MOSFET models and its various important parameters CO2: Illustrate the operation of MOS current mirror and single stage amplifier CO3: Analyze the performance parameter of Op-amp and differential amplifier. CO4: Determine the MOSFET operational challenges in the nanometer region CO5: Analyze the advantages and challenges in multi-gate devices. CO6: Compare various performance parameters of MOSFET and multi-gate devices							
Detailed Syllabus:							
Unit	Description						Duration
1.	Necessity and advantages of CMOS Analog Circuits, Overview of MOS amplifiers and their analysis; analysis of MOS circuits using square law; frequency response, bandwidth enhancement;						11
2.	Analog building blocks: MOS current mirror, cascade current mirrors, BW analysis and output impedance of CM, Single stage amplifier (SSA) configurations, cascode stage, Transconductance amplifier, frequency response.						9
3.	Differential amplifiers with MOS Loads, device mismatch effects, frequency response of differential amplifiers. Op-amp: Performance parameters, one & two-stage Op-amps, pole-zero compensation, gain boosting, active compensation, input range, slew rate, noise in op-amp.						11
4.	Advanced MOSFET: Silicon-On-Insulator (SOI) MOSFETs: Fully Depleted (FD) SOI, Partially Depleted (PD) SOI, Junction Less SOI						9
5.	MOSFET, multi-gate transistors: - single gate – double gate – triple gate – surround gate, quantum effects- advantages and challenges						11
6.	Digital circuits design, impact of device performance on digital circuits, leakage performance trade off, multi-VT devices and circuits.						9
	Total						60
Text Books: 1. Design of Analog CMOS Integrated Circuits, Behzad Razavi, McGraw Hill Indian, 2nd Edition (2017) 2. Wolf, W., “Modern VLSI Design System on Silicon”, 2nd Ed., Pearson Education 3. J P Colinge, “FINFETs and other multi-gate transistors”, Springer – Series on integrated circuits and systems, 2008.							

Reference Books:

1. CMOS Circuit Design: Layout and Simulation, R. Jacob Baker, Wiley IEEE Press, 3rd Edition (2010)
2. CMOS Analog Circuit Design, E. Allen & Douglas R. Holberg, Oxford Press Int. Edition, 3rd Edition (2012)
3. Jean- Pierre Colinge, Silicon-on-insulator Technology: Materials to VLSI, Kluwer Academic publishers' group.
4. Sandip Kundu, Aswin Sreedhar, "Nanoscale CMOS VLSI Circuits: Design for Manufacturability" McGraw Hill, 2010



Department of E&TC Engineering

Program:		B. Tech. (E&TC-Honors)			Semester: VI			
Course:		Analog Circuits and Advance MOS Devices Lab			Code: BET26HN12			
		Teaching Scheme (Hrs./Week)			Evaluation scheme and Marks			
Credit	Lecture	Practical		Tutorial	TW	OR	PR	Total
01	--	02		-	25	25	--	50
Prior knowledge of: Analog circuits and semiconductor devices								
Objectives: To analyze performance parameters of analog circuits To measure performance parameters of MOSFET and advanced CMOS devices with technology scaling								
Outcomes: At the end of Laboratory work, the students will be able to: CO 1: Measure various performance parameters of analog circuits. CO 2: perform transfer characteristics of MOSFET devices CO 3: Analyze the impact of technology scaling on MOSFET and Advanced CMOS devices.								
Detailed Syllabus:								
Expt. No.	List of Experiments							
1	Design and simulation of Single Stage Amplifier and transconductance plot							
2	Design and simulation of Common Source Amplifier							
3	Design and simulation of Single Stage Amplifier with different load							
4	Implementation of CMOS Inverter. Obtain & Plot Its Transfer Characteristics, Determine Noise Margins and Measure Propagation Delay.							
5	Design SRAM cell using MOSFET and analyze impact of short channel effects on its performance in nanometer region							
6	Implement and analyze I-V characteristics of FinFET using Microwind							
Reference Books:								
<ol style="list-style-type: none"> 1. R. Jacob Baker, CMOS: circuit Design, Layout and Simulation, Wiley, 2009 2. Douglas R. Holberg, Phillip E. Allen, CMOS Analog Design, 3rd Edition, Oxford University Press, 2013. 3. Brajesh Kumar Kaushik, Nanoscale Devices: Physics, Modeling, and Their Application, CRC Press, 2018 								



Course Syllabus

Semester – VII/VIII

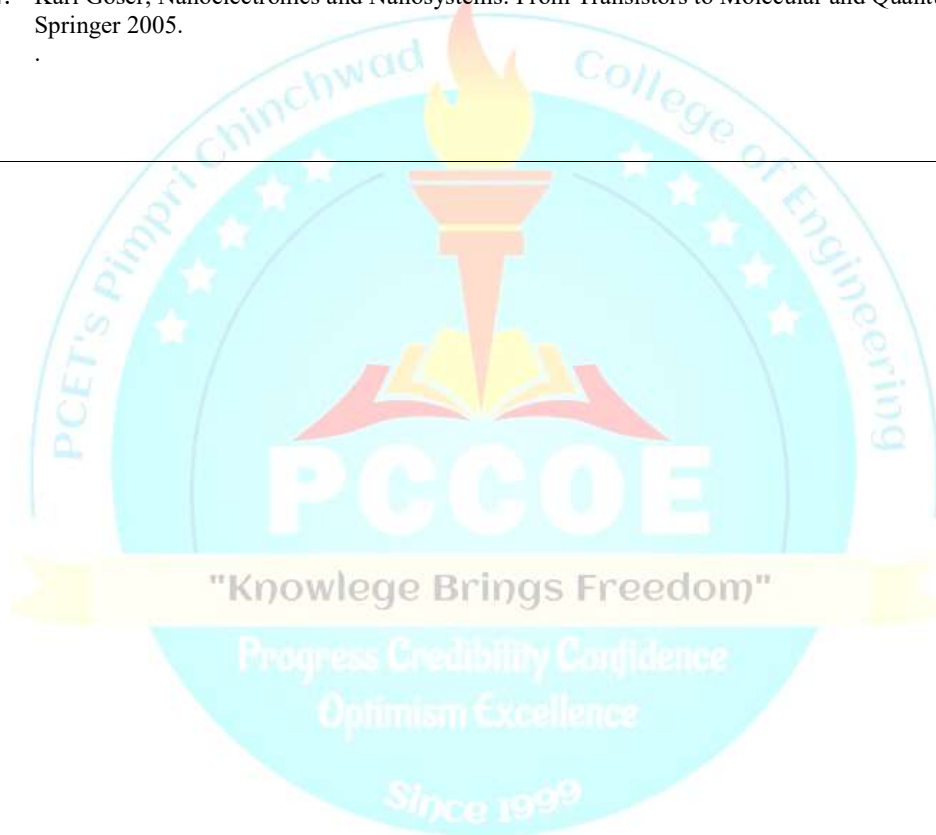
Program:	B. Tech. (E&TC) -Honors In Semiconductor Technology			Semester:	VI		
Course:	VLSI Physical Design and Fabrication Techniques			Code:	BET27HN11/ BET28HN12		
Teaching Scheme				Evaluation Scheme and Marks			
Credit	Lecture	Practical	Tutorial	FA		SA	Total
				FA1	FA2		
4	4	-	-	20	20	60	100
Prior Knowledge of:							
1. Semiconductor devices and circuits Is essential							
Course Objectives:							
1. Describe ASIC physical design flow for full custom and semi-custom design approach 2. Understand the process involved in semiconductor manufacturing and fabrication.							
Course Outcomes: After completion of this course Students should be able to :							
1. Understand the ASIC Physical design floor planning and placement algorithms 2. Explain the full custom and semicustom design concepts in VLSI physical design 3. Express process of clock tree synthesis and its distribution and routing 4. Identify different lithographic process in fabrication technology 5. Explain the processes- etching, oxidation, deposition involved in semiconductor manufacturing. 6. Understand the process flow for CMOS, PMOS, NMOS; and packaging functions and operations.							
Detailed Syllabus:							
Unit	Description						Duration
1.	ASIC physical design issues, System Partitioning, Floor planning and Placement. Algorithms: K-L-Kernigham-Lin's algorithm, FM- Fiduccia Mattheyses algorithm, Simulated annealing algorithms.						11
2.	Full Custom Design: Basics, Needs and Applications. Schematic and layout basics, Full Custom Design Flow. Semicustom Approach: Synthesis (RTL to Gate netlist) - Introduction to Constraints (SDC), Introduction to Static Timing Analysis (STA). Place and Route (Logical to Physical Implementation): Floorplan and Power-Plan.						9
3.	Placement, Clock Tree Synthesis- clock planning and distribution, Routing: Timing Optimization, GDS generation						11
4.	IC Technology: Crystal growth, Basic wafer fabrication operations, process yields, Semiconductor material preparation, Basic wafer fabrication operations, Yield measurement; Contamination sources, Clean room construction; Oxidation: dry oxidation, wet oxidation; Lithography. The Photolithographic Process, Photomask Fabrication, Comparison between positive and negative photoresists, Exposure Systems, Characteristics of Exposure Systems, E-beam Lithography, X-ray lithography.						9
5.	Etching: Dry etching, Wet etching, resist stripping; Doping: Diffusion process steps, deposition, Drive-in oxidation, Ion implantation-1, Ion implantation-2; Deposition: CVD basics, CVD process steps, Low pressure CVD systems, Plasma enhanced CVD systems, Vapour phase epitaxy, molecular beam epitaxy; Chemical mechanical polishing; Metallization.						11
6.	Process flow for NMOS, PMOS, CMOS, BICMOS ICs, Novel MOS and GaN based devices. Design rules, stick diagrams and layout. Packaging: Chip characteristics, package functions, package operations						9
Total						60	

Text Books:

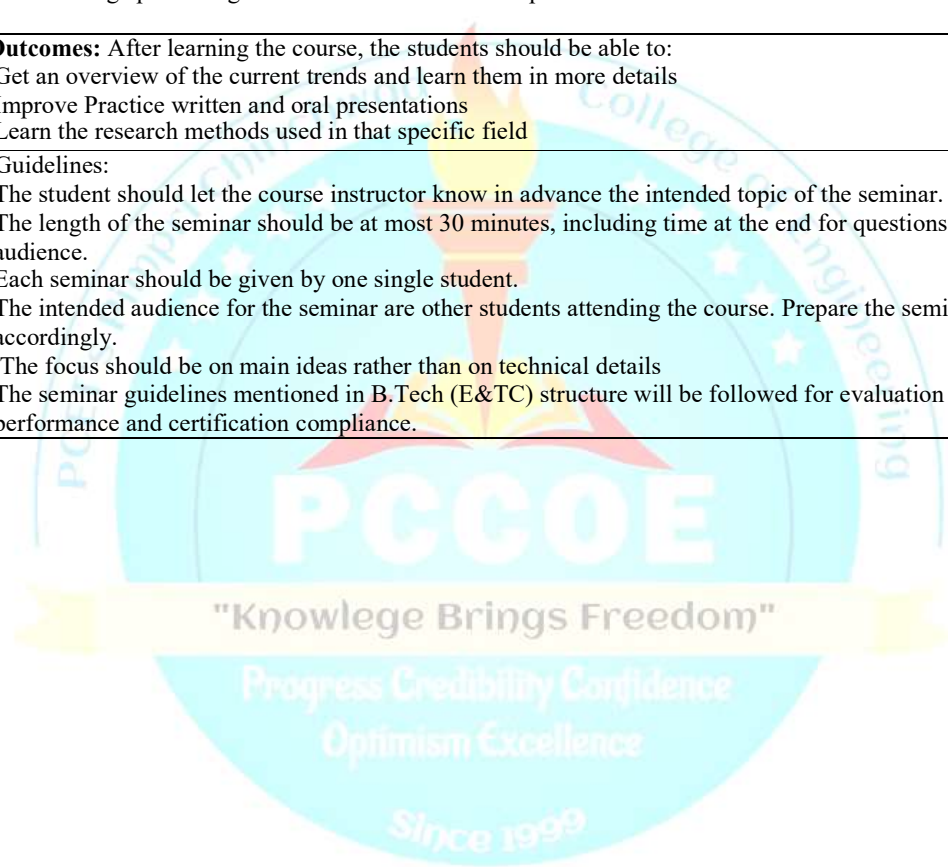
1. H.Gerez, "Algorithms for VLSI Design Automation", John Wiley, 1999
2. Sarrafzadeh, M. and Wong, C.K., "An Introduction to VLSI Physical Design", 4th Ed., McGraw-Hill.
3. S.M. Sze, VLSI technology, Tata McGraw-Hill, Second Edition, 2017. 2. R.C. Jaeger, Introduction to microelectronic fabrication, Prentice Hall, Second Edition, 2013.

Reference Books:

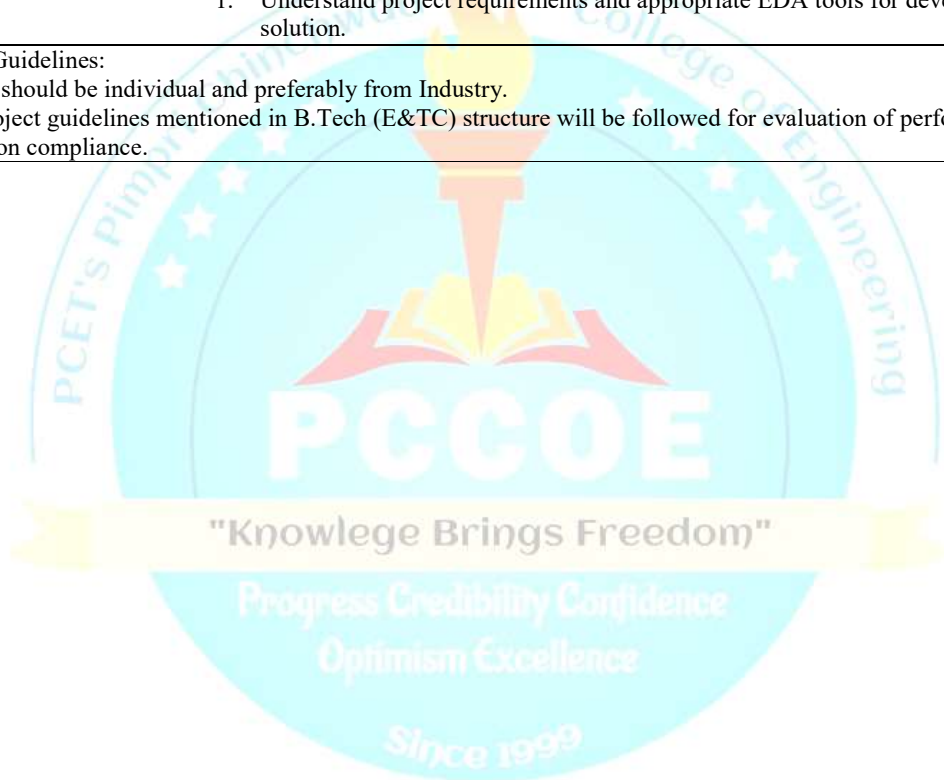
1. Sait, S.M. and Youssef, H., "VLSI Physical Design Automation: Theory and Practice", World Scientific.
2. Sherwani, N.A., "Algorithm for VLSI Physical Design Automation", 2nd Ed., Kluwer.
3. Wong, B.P., Mittal, A., Cao Y. and Starr, G., "Nano-CMOS Circuit and Physical Design", Wiley.
4. Karl Goser, Nanoelectronics and Nanosystems: From Transistors to Molecular and Quantum Devices, Springer 2005.



Program:	B. Tech. (E&TC) -Honors in Semiconductor Technology			Semester:	VII /VIII	
Course:	Seminar			Code:	BET27HN12/ BET28HN13	
Teaching Scheme (Hrs./Week)			Evaluation Scheme and Marks			
Credit	Lecture	Practical	FA2	TW	OR	Total
2	-	-			50	50
Course Objectives:						
<ol style="list-style-type: none"> 1. To identify practical learning skills and concepts and learn to communicate it to society. 2. To encourage personal growth of students and development of effective communication skills 						
Course Outcomes: After learning the course, the students should be able to:						
<ol style="list-style-type: none"> 1. Get an overview of the current trends and learn them in more details 2. Improve Practice written and oral presentations 3. Learn the research methods used in that specific field 						
Detailed Guidelines:						
<ol style="list-style-type: none"> 1. The student should let the course instructor know in advance the intended topic of the seminar. 2. The length of the seminar should be at most 30 minutes, including time at the end for questions from the audience. 3. Each seminar should be given by one single student. 4. The intended audience for the seminar are other students attending the course. Prepare the seminar accordingly. 5. The focus should be on main ideas rather than on technical details 6. The seminar guidelines mentioned in B.Tech (E&TC) structure will be followed for evaluation of performance and certification compliance. 						



Program:	B. Tech. (E&TC) -Honors in Semiconductor Technology			Semester:	VII /VIII	
Course:	Project			Code:	BET28HN11/ BET27HN13	
Teaching Scheme (Hrs./Week)			Evaluation Scheme and Marks			
Credit	Lecture	Practical	FA2	TW	OR	Total
4	-	-	-	100	50	150
Prior Knowledge of: Information management, Machine Learning and IoT is essential.						
Course Objectives:						
<ol style="list-style-type: none"> 1. To emphasize on project implementation to realize acquired knowledge and skills using suitable EDA tools. 2. To provide platform to students to demonstrate and effectively communicate their knowledge. 						
Course Outcomes: After learning the course, the students should be able to:						
<ol style="list-style-type: none"> 1. Understand project requirements and appropriate EDA tools for developing the solution. 						
Detailed Guidelines:						
<ol style="list-style-type: none"> 1. Project should be individual and preferably from Industry. 2. The project guidelines mentioned in B.Tech (E&TC) structure will be followed for evaluation of performance and certification compliance. 						



Vision and Mission of E&TC Engineering Department

VISION:

To be recognized as a distinguished department in the field of electronics and telecommunication transforming students into competent technocrats by providing an Ethical, Sustainable and Value-Added Quality Education.

MISSION:

1. To create competent Electronics and Tele-communication engineers with Knowledge, Skill and Attitude by establishing a conducive learning environment.
2. To nurture technical competency, entrepreneurship skills and promote higher studies through the state-of-art facilities for building successful careers.
3. To facilitate research by engaging in projects of industrial requirement and national importance.
4. To impart Life skills, Ethical and Social values for self-sustainability.